EECE - HWS Solutions

$$\frac{\Pr{oblem 1:}}{(a) \quad n \gg p, \text{ therefore : } n + N_{A} = p + N_{0} \approx N_{0}$$

$$\implies n \approx N_{0} - N_{A} = 10^{17} \text{ cm}^{-3} - 10^{15} \text{ cm}^{-3} = 9.9 \times 10^{16} \text{ cm}^{-3} \text{ m}^{-1} \text{ m}^{-1} = \frac{n \cdot 2}{n} = \frac{(1.45 \times 10^{10} \text{ cm}^{-3})^{2}}{9.9 \times 10^{16} \text{ cm}^{-3}} = 2.124 \times 10^{-3} \text{ cm}^{-3} = p$$

$$\frac{b}{N_{A}} = N_{0} \implies n = p = n \cdot = 1.45 \times 10^{10} \text{ cm}^{-3}$$

$$\frac{P_{roblem 2}}{V_{BE}} = \frac{e_{quothon} + 1}{1 \cdot (E_{E} + 1)} = 26 \times 10^{10} \text{ cm}^{-3} + 1)$$

$$\frac{V_{BE}}{V_{BE}} = 658.54 \text{ mV}$$

From page 212 in the book:  $U_{BC} = U_{BE} - U_{CE} = 0.65854V - 10V = \left[-9.341V = U_{BC}\right]$ The transistor operates in the active region because UCE > 0.2V and  $iB = \left[1 - \alpha\right] \cdot iE > 0$ , where  $\alpha = \frac{B}{1+B} = \frac{100}{101} = \left[0.990099 = \alpha\right]$   $iB = \left(1 - 0.990099\right) \cdot 10 \times 10^{-3}A = \left[99.0099 \mu A = iB\right]$  $ic = \alpha \cdot iE = 0.990099 \times 10 \pi A = \left[9.90099 \mu A = iC\right]$ 

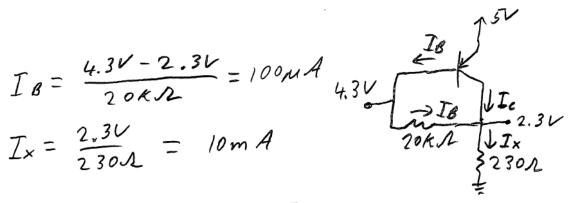
(p.)

(P.2) Problem 3  
a) 
$$\beta = 100$$
, equivalent circuit assuming earnahim if the active  
region:  
 $I_{0} = 100$ , equivalent circuit assuming earnahim if the active  
 $I_{0} = 100$ ,  $I_{0} = 10$ 

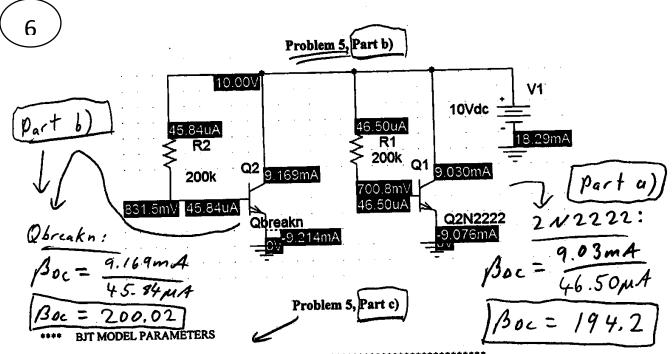
... Problem 3 cont.: b) with B= 300, assuming saturation: part IL \$15V Ix = 15V-0.7V = 30.426 MA VCE = 0.2V  $I_{y} = \frac{-15V-0.7V}{1MR} = -15.7 \mu 4$ Ix & 4 TOKA (F)0.2V IB = Ix + Ing = 14.73 part 20 (condition) IB = Ix + Ing = 14.73 part 20 (is met) [SIML  $I_{c} = \frac{15V - 0.2V}{6.8KA} = 2.176 \text{ mA} = I_{c}$ Iy V-15V The BJT is in saturation because condition 2 is satisfied: B.I.B>Ic>0 > 4.419mA > 2.176mA >0  $I_{x} V_{x}^{15V} I_{y} J_{x}^{15V} I_{x} = \frac{15V - (-15V)}{1MN + 470KN} = 20.408 \mu A$ = 100, assuming cutoff: C $V_{B} = 15V - I_{x} \cdot I_{M} \Lambda = -5.408V$ VBE = VB - VE = -5.408 V < 0.5V La condition 1 is satisfied IN 3470KA VBC = VB - VC = -5.408V - 15V = -20.408V1Ē 6 condition 2 is met a confirms cutoff Ie = 0 VBC<0.5V  $V_{CE} = V_{C} - OV = [15V = V_{CE}]$ B= 300 , assuming cuttoff: -> same analysis as with B=300 IJEORA 115V IXLAIMA  $|I_c = 0|$ Vee = 15V ₽E

... Problem 3 cont .: d) B=100, assuming active:  $I_{B} = I_{IE} \quad KUL: \quad 0 = -I_{B} \cdot 220 k R - 0.7U + 15U$   $I_{B} = \frac{15V - 0.7U}{220 \times 10^{3} R} = 65 \times 10^{-6} A$   $I_{B} = \frac{15V - 0.7U}{220 \times 10^{3} R} = 65 \times 10^{-6} A$   $I_{B} = 0.7U$   $I_{B} = 0.7U$ IB>0 -> condition 1 is met  $C = \beta \cdot I_B = 100 \cdot 65 \mu A = 6.5 m A = I_C$ Vc = Ic · 1 K ~ = 6,5V  $V_{CE} = V_C - V_E = 6.5V - 15V = [-8.5V = V_{CE}]$ 31KA check of condition 2: VCE < = 0.2V -> confirms B=300, assuming saturation: IB = 15V-0.7V = 65µA 70 (condition 1) IB = 220KR = 65µA 70 (is met) IB E VIE B III 220KA = 0.2V C VIE  $KVL: 0 = -15V + 0.2V + I_c \cdot 1K\Lambda$   $\rightarrow I_c = \frac{15V - 0.2V}{1000 \Lambda} = 14.$ -> Ic = 150-0.20 = [14.8 mA=Ic] check for condition 2: 3182 B.IB> Ic 70 19.5mA > 14.8mA >0 -> confirms Sqturation Vc = 14.8mA. 1KN = 14.8V  $V_{CE} = V_{C} - V_{E} = 14.8V - 15V = -0.2V$ VCE = - 0.2V





KCL:  $I_{x} = I_{B} + I_{C}$   $() I_{c} = I_{x} - I_{B} = 10mA - 100mA = 9.9mA$  $\beta = \frac{I_{c}}{T_{A}} = \frac{9.9mA}{100mA} = \frac{99}{79} = \beta$ 



Q2N2222 Qbreakn NPN NPN IS 100.00000E-18 14.340000E-15 255.9 **BF** 200 1 NF 1 74.03 VAF .2847 IKF 14.340000E-15 ISE 1.307 NE 6.092 BR 1 NR 1 1 RB 10 RC 1 22.010000E-12 CJE MJE .377 7.306000E-12 CJC .3416 MJC 411.100000E-12 TF XTF 3 1.7 VTF ITF .6 46.910000E-09 TR 1.5 ΧТВ 2.42 CN 2.42 .87 D.87

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- part c

OPERATING POINT INFORMATION TEMPERATURE = 27.000 DEG C

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### **\*\*\*\*** BIPOLAR JUNCTION TRANSISTORS

NAME Q\_Q1 Q\_Q2 MODEL Q2N2222 Qbreakn 4.65E-05 4.58E-05 IB IC 9.03E-03 9.17E-03 7.01E-01 8.32E-01 VBE -9.30E+00 -9.17E+00 1.00E+01 1.00E+01 VBC VCE 3.40E-01 3.54E-01 GM RPI 5.99E+02 5.64E+02 1.00E+01 0.00E+00 RX 9.23E+03 1.00E+12 RO 1.78E-10 0.00E+00 CBE 3.01E-12 0.00E+00 CBC 0.00E+00 0.00E+00 CJS

-> BETAAC 2.04E+02 2.00E+02 CBX/CBX2 0.00E+00 0.00E+00 FT/FT2 2.99E+08 5.64E+18

part c)

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Problem 5, Part d)

Philips Semiconductors

8

Product specification

# NPN switching transistors

# 2N2222; 2N2222A

SYMBOL	nless otherwise specified. PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Сво	collector cut-off current				nA	
		IE = 0; VCB = 50 V	<u> −</u>	10		
		I <sub>E</sub> = 0; V <sub>CB</sub> = 50 V; T <sub>amb</sub> = 150 °C	<u>  -</u>	10		
ICBO	collector cut-off current			140		
		I <sub>E</sub> = 0; V <sub>CB</sub> = 60 V		10	nA uA	
		IE = 0; VCB = 60 V; Tamb = 150 °C		10		
I <sub>EBO</sub>		I <sub>C</sub> = 0; V <sub>EB</sub> = 3 V		10	nA	<u></u>
hfe	DO content gen	Ic = 0.1 mA; VcE = 10 V	35	-  _		$ k\rangle$
		$\frac{I_{C} = 1 \text{ mA; } V_{CE} = 10 \text{ V}}{I_{C} = 10 \text{ mA; } V_{CE} = 10 \text{ V}}$ $\frac{I_{C} = 150 \text{ mA; } V_{CE} = 10 \text{ V}}{I_{C} = 150 \text{ mA; } V_{CE} = 10 \text{ V; note 1}}$ $\frac{I_{C} = 150 \text{ mA; } V_{CE} = 10 \text{ V; note 1}}{I_{C} = 10 \text{ V; note 1}}$	50		+	Snot
		Ic = 10 mA; Vc= = 10 V	75	<b>↓</b>		1+6,
	Boc for this	Ic = 150 mA; Vce = 1 V; note 1	50	-	<u> </u>	S'nothe the
	Case	Ic = 150 mA; VcE = 10 V; note 1	100	300	+	y varn
hfe	DC current gain 2N2222A	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 10 V; T <sub>amb</sub> = -55 °C	35			
h	DC current gain	Ic = 500 mA; VcE = 10 V; note 1		1		1
1.445	2N2222		30	1-		
	2N2222A		40	-	1	1
VCEset	collector-emitter saturation voltage					
*CEss(	2N2222	Ic = 150 mA; Is = 15 mA; note 1		400	mV	
		1c = 500 mA; Ig = 50 mA; note 1	-	1.6	V	4
V <sub>CEsst</sub>	collector-emitter saturation voltage	}				1
	2N2222A	I <sub>C</sub> = 150 mA; I <sub>B</sub> = 15 mA; note 1	-	300	mV	_
1		Ic = 500 mA; IB = 50 mA; note 1	-	1	<u>v</u>	
VBEsat	base-emitter saturation voltage		Ţ			
V BEsat	2N2222	I <sub>C</sub> = 150 mA; I <sub>B</sub> = 15 mA; note 1	-	1.3	V	
1		I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; note 1		2.6	V	4
VBEset	base-emitter saturation voltage					
	2N2222A	Ic = 150 mA; Is = 15 mA; note 1	0.6	1.2	<u> </u>	
		Ic = 500 mA; Ig = 50 mA; note 1	-	2	<u>v</u>	1
	collector capacitance	IE = ie = 0; VCB = 10 V; f = 1 MHz		8	pF	
C <sub>c</sub>	emitter capacitance	$i_{C} = i_{c} = 0; V_{EB} = 500 \text{ mV}; f = 1 \text{ MHz}$				
<b>1</b>	2N2222A			25	pF	_
fT	transition frequency	1 <sub>C</sub> = 20 mA; V <sub>CE</sub> = 20 V; f = 100 MHz	1			
<b>[</b> "	2N2222	-	250	1-	MHz	
	2N2222A		300		MHz	_
F	noise figure	$l_{c} = 200 \ \mu A; V_{CE} = 5 \ V; R_{S} = 2 \ k\Omega;$				1
1.	2N2222A	f = 1 kHz; B = 200 Hz	1_	4	dB	1

1997 May 29